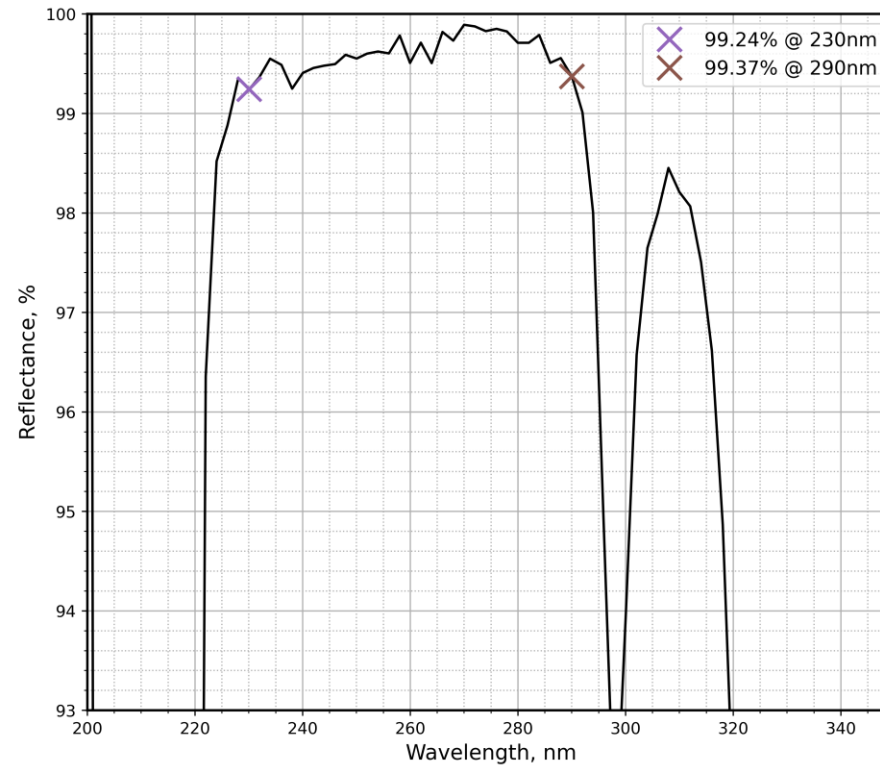


S1: HRs>98.5%@230-290 nm + HTp>95%@460-580+1100-1600 nm + HTs>80%@760-830nm + HTs>70%@1600-2600 nm, AOI = 60 deg. GDD < 30 fs  
S2: ARsp



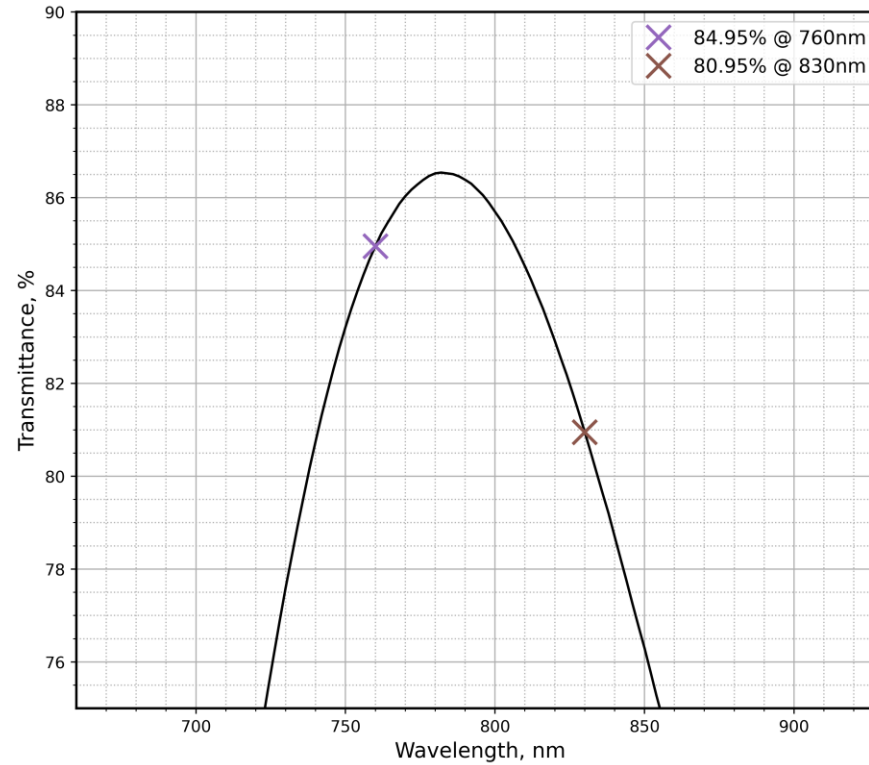
PO6143 Rs i60

Fig. 1.

SIDE MEASURED: S1+S2 (good component)

COMMENTS: Margin of measurement error: +/-0.25%

S1: HRs>98.5%@230-290 nm + HTp>95%@460-580+1100-1600 nm + HTs>80%@760-830nm + HTs>70%@1600-2600 nm, AOI = 60 deg. GDD < 30 fs  
S2: ARsp



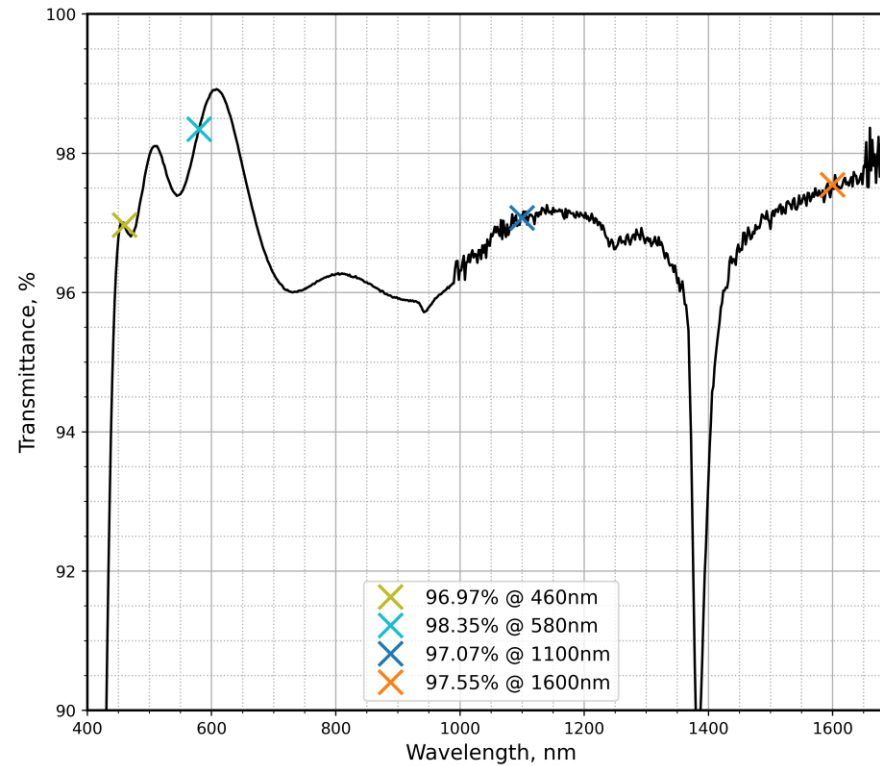
PO6143 Ts i60

Fig. 2.

SIDE MEASURED: S1+S2 (good component)

COMMENTS: Margin of measurement error: +/-0.25%

S1: HRs>98.5%@230-290 nm + HTp>95%@460-580+1100-1600 nm + HTs>80%@760-830nm + HTs>70%@1600-2600 nm, AOI = 60 deg. GDD < 30 fs  
S2: ARsp



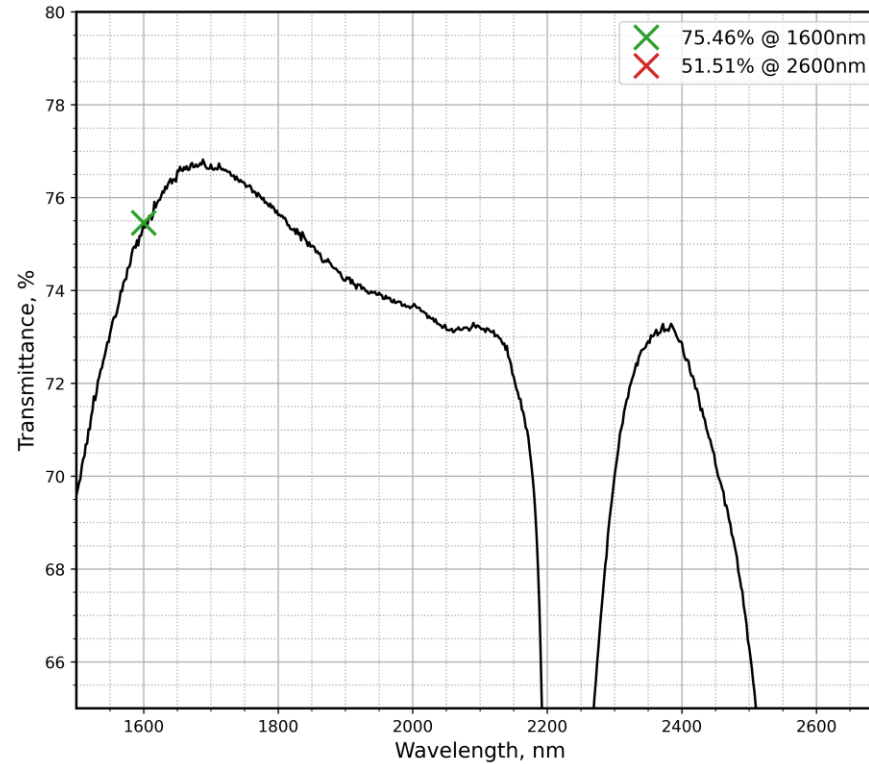
PO6143 Tp i60

Fig. 3.

SIDE MEASURED: S1+S2 (good component)

COMMENTS: Margin of measurement error: +/-0.25%; [Absorption at 1400nm coming from UVFS substrate](#)

S1: HRs>98.5%@230-290 nm + HTp>95%@460-580+1100-1600 nm + HTs>80%@760-830nm +HTs>70%@1600-2600 nm, AOI = 60 deg. GDD < 30 fs  
S2: ARsp



PO6143 Ts i60

Fig. 4.

SIDE MEASURED: S1+S2 (good component)

COMMENTS: Margin of measurement error: +/-0.25%; Absorption lines >2100nm coming from UVFS substrate